



DMP2005UFG

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C		
2014	4.0mΩ @ V _{GS} = -4.5V	-89A		
-20V	6.5mΩ @ V _{GS} = -2.5V	-70A		

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch
- Power Management Functions

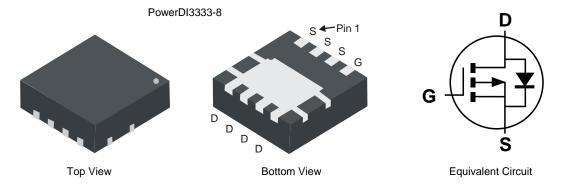
20V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Features

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor, thermally efficient package enables higher density end products (PowerDI®)
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2005UFG-7	PowerDI3333-8	2,000/Tape & Reel
DMP2005UFG-13	PowerDI3333-8	3,000/Tape & Reel

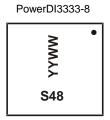
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



S48 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value -20	Units V		
Drain-Source Voltage	V _{DSS}				
Gate-Source Voltage	V _{GSS}	±10	V		
Continuous Drain Current V_{GS} = -4.5V (Note 7)	Steady State	T _C = +25°C T _C = +70°C	ID	-89 -70	А
Continuous Drain Current V_{GS} = -4.5V (Note 6)	Steady State	T _A = +25°C T _A = +70°C	ID	-19 -15	А
Pulsed Drain Current (380µs pulse, duty cycle = 1%)	I _{DM}	-100	А		
Maximum Continuous Body Diode Forward Current (ls	-2.5	А		
Avalanche Current (Note 8) L = 0.1mH	I _{AS}	-27	А		
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	35	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ extsf{ heta}JA}$	128	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ ext{ heta}JA}$	57	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	PD	48	W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	2.6	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	—	-	-1	μA	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-0.3	-0.7	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	3.5	4.0		V _{GS} = -4.5V, I _D = -15A	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	5.4	6.5	mΩ	$V_{GS} = -2.5V, I_D = -10A$	
		_	8.0	14		$V_{GS} = -1.8V, I_D = -1A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$	
DYNAMIC CHARACTERISTICS (Note 10)						-	
Input Capacitance	Ciss	_	4,670	_		$V_{DS} = -10V$, $V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	—	650	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	550	_			
Gate Resistance	R _G	_	3.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)							
Total Gate Charge (V _{GS} = -10V)	Qg	_	125	_			
Gate-Source Charge	Q _{gs}	_	7.8	_	nC	$V_{DD} = -10V, I_D = -20A$	
Gate-Drain Charge	Q _{gd}	_	16.5	_			
Turn-On Delay Time	t _{D(ON)}	_	9.5	_			
Turn-On Rise Time	t _R	_	10.5		1	$V_{GS} = -4.5V, V_{DD} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	115	_	ns	$R_G = 1\Omega$, $R_G = 1\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _F	_	85		1		
Reverse Recovery Time	t _{RR}	_	25	_	ns	I _F = -10A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}	_	14	_	nC	I _F = -10A, di/dt = 100A/µs	

Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

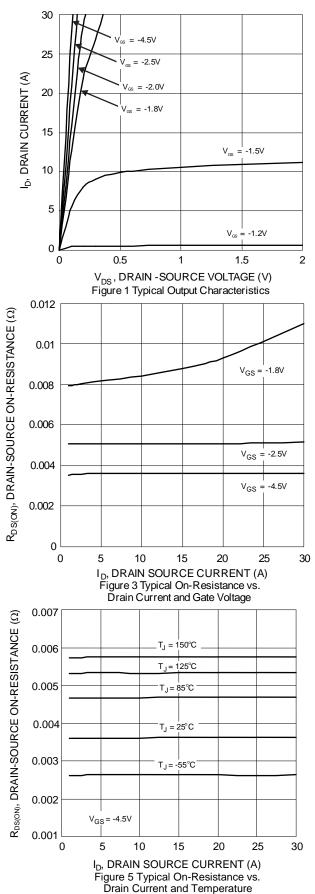
8. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

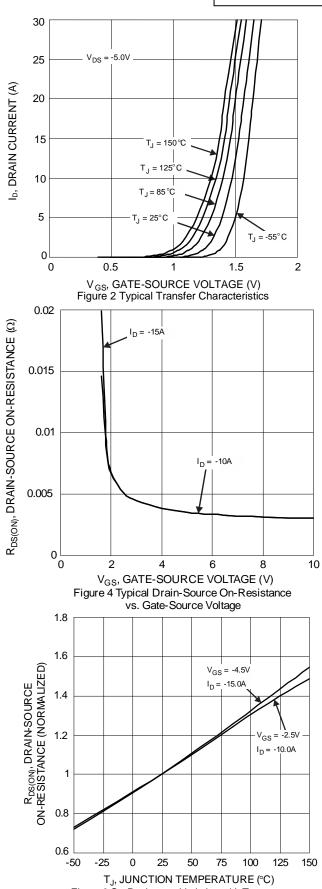
9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

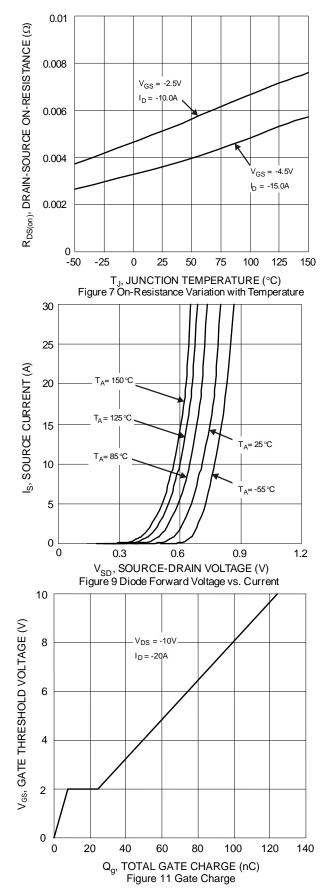


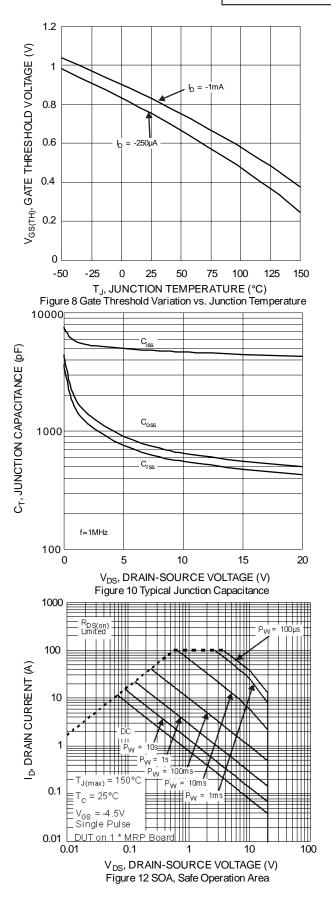




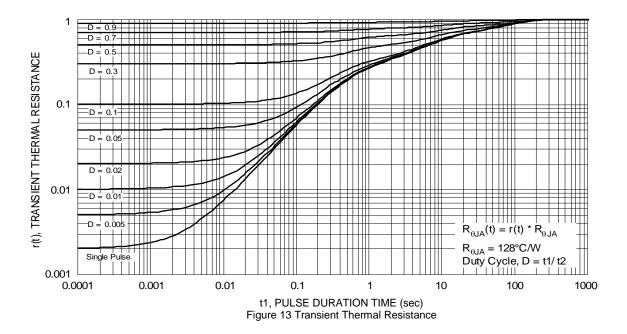








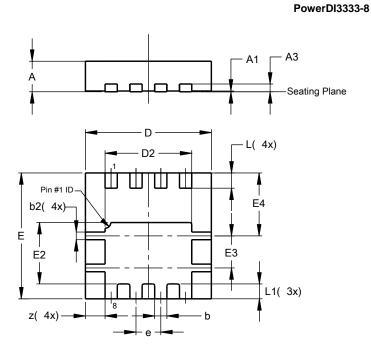






Package Outline Dimensions

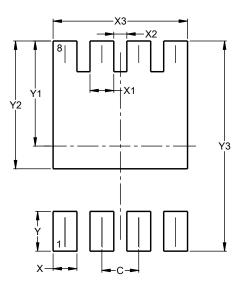
Please see http://www.diodes.com/package-outlines.html for the latest version.



	PowerDI3333-8						
Dim	Min	Max	Тур				
Α	0.75	0.85	0.80				
A1	0.00	0.05	0.02				
A3	1	-	0.203				
b	0.27	0.37	0.32				
b2	0.15	0.25	0.20				
D	3.25	3.35	3.30				
D2	2.22	2.32	2.27				
Е	3.25	3.35	3.30				
E2	1.56	1.66	1.61				
E3	0.79	0.89	0.84				
E4	1.60	1.70	1.65				
е	e – – 0.6		0.65				
L	0.35	0.45	0.40				
L1	_	_	0.39				
z	_	-	0.515				
All I	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8

Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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